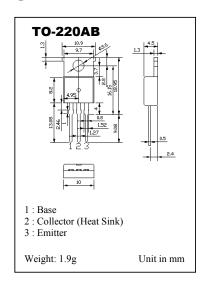


## NPN SILICON TRIPLE DIFFSUED TRANSISTOR

...designed for audio frequency power amplifier applications.

#### **MAXIMUM RATINGS** (Ta = 25 °C)

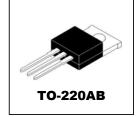
Characteristic	Symbol	Value	Unit
Collector Base Voltage	Vсво	60	V
Collector Emitter Voltage	VCEO	60	V
Emitter Base Voltage	VEBO	7	V
Collector Current	Ic	3	Α
Base Current	Ів	0.5	Α
Collector Power Dissipation T <sub>a</sub> = 25 °C	Pc	1.5	W
Collector Power Dissipation Tc = 25 °C	Pc	30	W
Junction Temperature	Tj	150	°C
Storage Temperature Range	Tstg	-55 ~ 150	°C



#### **ELECTRICAL CHARACTERISTICS** (Ta = 25 °C)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Collector Cutoff Current	Ісво	V <sub>CB</sub> =60V, I <sub>E</sub> =0	-	-	100	μА
Emitter Cutoff Current	ІЕВО	VEB=7V, IB=0	-	-	100	μА
Collector Emitter Breakdown	V(BR)CEO	Ic=50mA, IB=0	60	-	1	V
Voltage						
DC Current Gain	hfE	Vce=5V, Ic =0.5A	60	-	300	i
Collector Emitter Saturation	VCE(sat)	Ic =3A, IB=0.3A	-	0.25	1	V
Voltage						
Base Emitter Voltage	VBE	VCE =5V, IC =0.5A	-	0.7	1	V
Transition Frequency	fτ	VCE =5V, IC =0.5A	-	3	ı	MHz
Collector Output Capacitance	Cob	Vce =10V, Ie=0, f=1MHz	-	70	ı	pF
Switching Time						
Turn On Time	ton		-	8.0	-	μS
Storage Time	<b>t</b> stg		-	1.5	-	μS
Fall Time	tf		-	0.8	-	μS

# NPN SILICON TRIPLE DIFFSUED TRANSISTOR



### **CLASSIFICATIONS OF hFE**

Rank	0	Υ	GR
Range	60 to 120	100 to 200	150 to 300

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